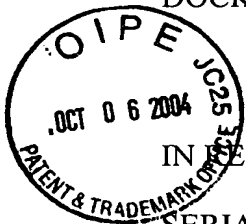


DOCKET NO.: 219030US2S/hyc



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF: Toshitake YAEGASHI

SERIAL NUMBER: 10/058,343

GROUP: 2814

FILED: January 30, 2002

EXAMINER: Marcos D. PIZARRO
CRESPO

FOR: NON-VOLATILE SEMICONDUCTOR MEMORY DEVICE IN WHICH
SELECTION GATE TRANSISTORS AND MEMORY CELLS HAVE DIFFERENT
STRUCTURES

REQUEST TO CORRECT TITLE OF INVENTION

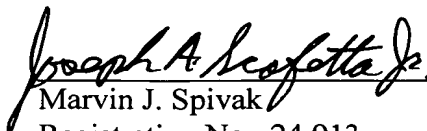
MAIL STOP ISSUE FEE
COMMISSIONER FOR PATENTS
P.O. BOX 1450
ALEXANDRIA, VA 22313-1450

SIR:

In the matter of the above-identified application for patent, we hereby request
correction of your records to reflect the correct title of the invention. The title of the
invention should read as follows: NON-VOLATILE SEMICONDUCTOR MEMORY
DEVICE IN WHICH SELECTION GATE TRANSISTORS AND MEMORY CELLS
HAVE DIFFERENT STRUCTURES.

Respectfully Submitted,

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